



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of)

Kichiya TANINO et al.)

Appln. No.: 09/771,556) Art Unit: 1765

Filed: January 30, 2001) Ex: R.M. Kunemund

For: SINGLE CRYSTAL SiC AND A)
METHOD OF GROWING THE SAME)

RESPONSE

Honorable Commissioner of Patents and Trademarks
Washington, D.C. 20231

Sir:

The following amendments and remarks are being submitted herewith in
accordance with the provisions of 37 CFR 1.111 in response to the Office Action of March 29,
2002.

AMENDMENT

IN THE SPECIFICATION:

Please replace the last two paragraphs on page 4 with the following:

--In order to attain the above-mentioned object, the single crystal SiC according to a first
aspect of the invention is characterized in that heat treatment is performed in an inert gas
atmosphere under a state where a cutting plane of a single crystal α -SiC substrate which is formed
by cutting along $(1, 1, \bar{2}, 0)$ Miller index plane $\pm 10^\circ$, and $(2, 2, 0)$ Miller index plane of a
polycrystalline β -SiC plate are superimposed on each other, whereby single crystal having a

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